

# IRF7726PbF

HEXFET<sup>®</sup> Power MOSFET

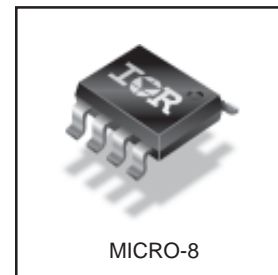
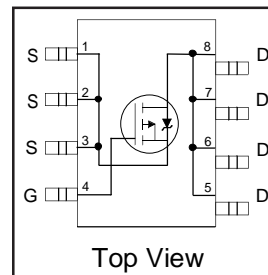
- Ultra Low On-Resistance
- P-Channel MOSFET
- Very Small SOIC Package
- Low Profile (< 1.2mm)
- Available in Tape & Reel
- Lead-Free

$V_{DS}$	$R_{DS(on) \max}$	$I_D$
-30V	0.026@ $V_{GS} = -10V$	-7.0A
	0.040@ $V_{GS} = -4.5V$	-6.0A

## Description

HEXFET<sup>®</sup> Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the ruggedized device design, that International Rectifier is well known for, provides the designer with an extremely efficient and reliable device for battery and load management.

The new Micro8 package, with half the footprint area of the standard SO-8, provides the smallest footprint available in an SOIC outline. This makes the Micro8 an ideal device for applications where printed circuit board space is at a premium. The low profile (<1.2mm) of the Micro8 will allow it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-7.0	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-5.7	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	-28	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation <sup>③</sup>	1.79	W
$P_D @ T_A = 70^\circ C$	Maximum Power Dissipation <sup>③</sup>	1.14	W
	Linear Derating Factor	0.01	W/ $^\circ C$
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to +150	$^\circ C$

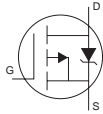
## Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient <sup>③</sup>	70	$^\circ C/W$

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.016	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA
R <sub>DSON</sub>	Static Drain-to-Source On-Resistance	—	—	0.026	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -7.0A ②
		—	—	0.040		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -6.0A ②
V <sub>GS(th)</sub>	Gate Threshold Voltage	-1.0	—	-2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
g <sub>fs</sub>	Forward Transconductance	10	—	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -7.0A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-15	μA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
		—	—	-25		V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 70°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-100	nA	V <sub>GS</sub> = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V <sub>GS</sub> = 20V
Q <sub>g</sub>	Total Gate Charge	—	46	69	nC	I <sub>D</sub> = -7.0A
Q <sub>gs</sub>	Gate-to-Source Charge	—	8.0	—		V <sub>DS</sub> = -15V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	8.1	—		V <sub>GS</sub> = -10V
t <sub>d(on)</sub>	Turn-On Delay Time	—	15	23	ns	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V
t <sub>r</sub>	Rise Time	—	25	38		I <sub>D</sub> = -1.0A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	227	341		R <sub>G</sub> = 6.0Ω
t <sub>f</sub>	Fall Time	—	107	161		R <sub>D</sub> = 15Ω ②
C <sub>iss</sub>	Input Capacitance	—	2204	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	341	—		V <sub>DS</sub> = -25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	220	—		f = 1.0MHz

## Source-Drain Ratings and Characteristics

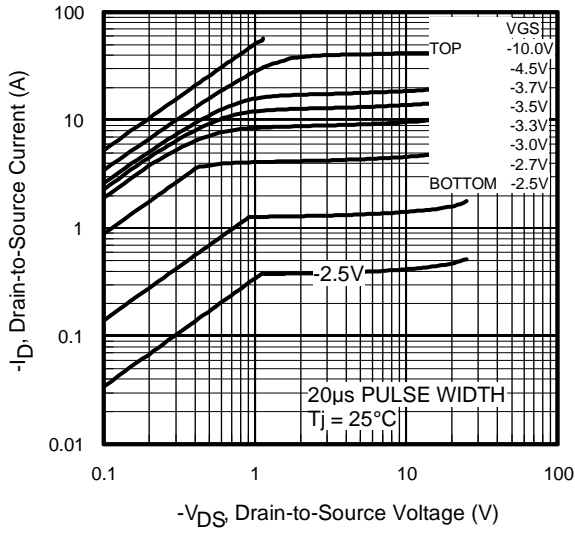
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-1.8	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	-28		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -1.8A, V <sub>GS</sub> = 0V ②
t <sub>rr</sub>	Reverse Recovery Time	—	35	53	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -1.8A
Q <sub>rr</sub>	Reverse Recovery Charge	—	32	48	μC	di/dt = -100A/μs ②

### Notes:

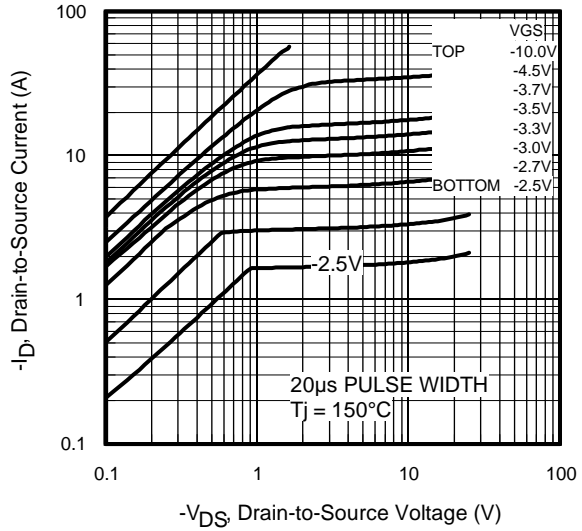
① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width ≤ 400μs; duty cycle ≤ 2%.

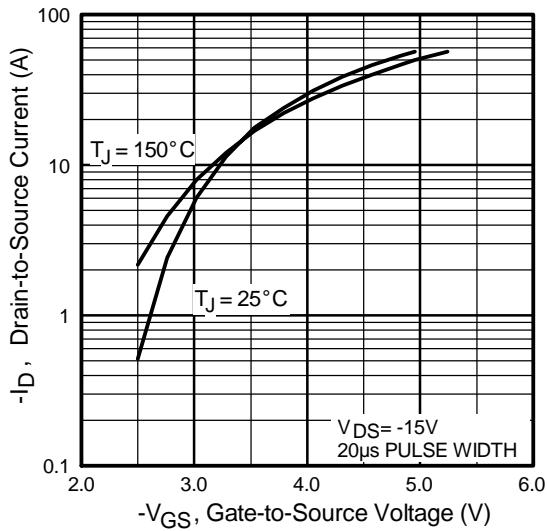
③ When mounted on 1 inch square copper board, t < 10 sec.



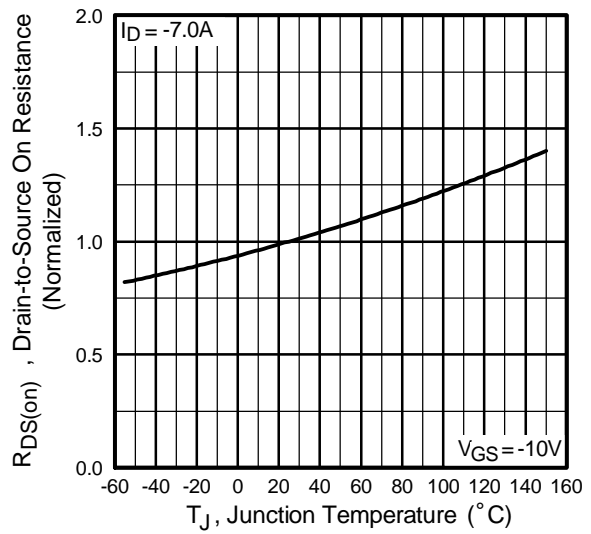
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



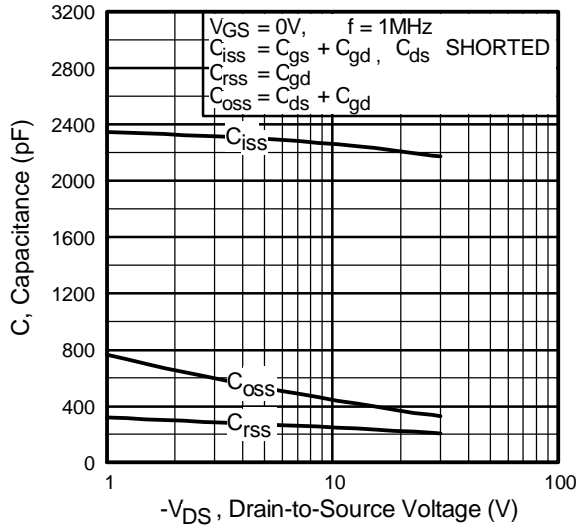
**Fig 3.** Typical Transfer Characteristics



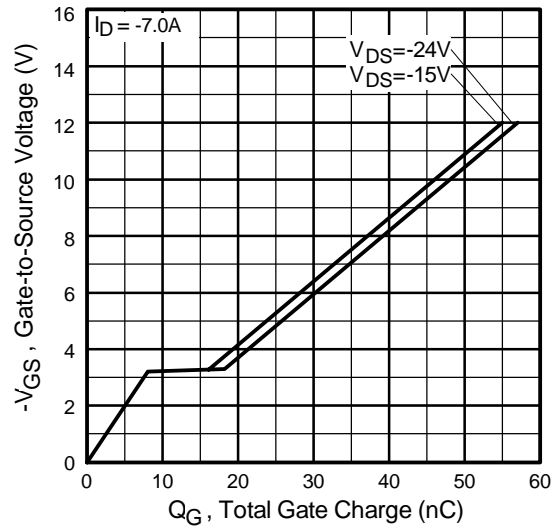
**Fig 4.** Normalized On-Resistance Vs. Temperature

# IRF7726PbF

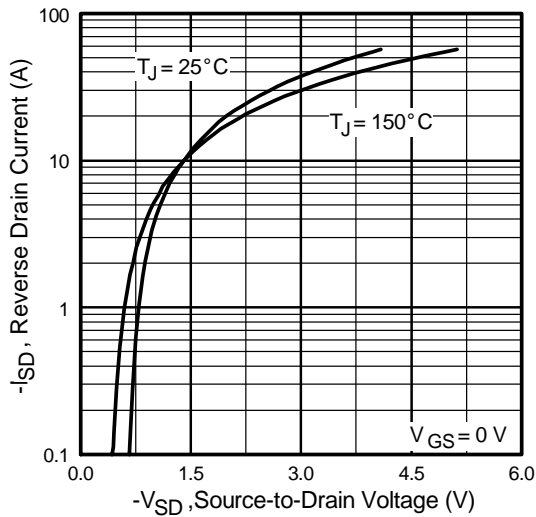
International  
**IR** Rectifier



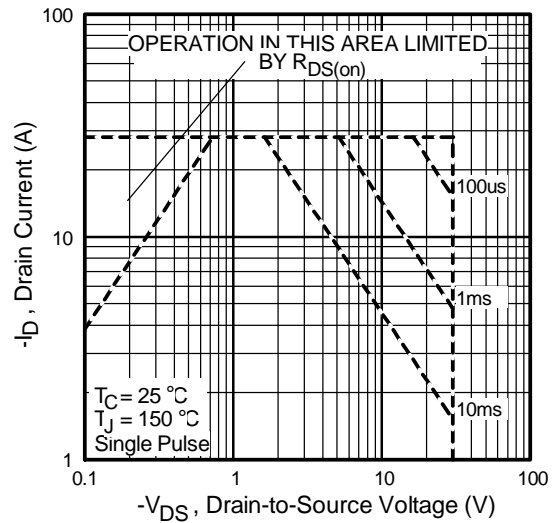
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



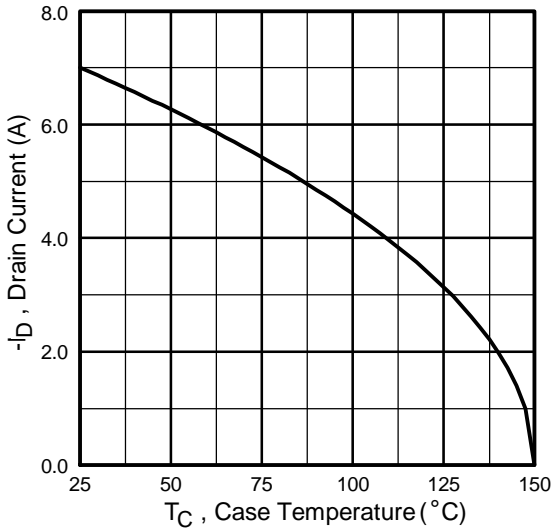
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



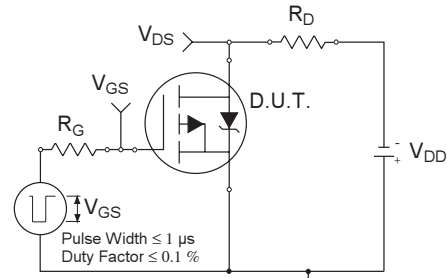
**Fig 7.** Typical Source-Drain Diode Forward Voltage



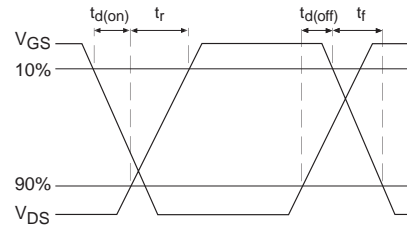
**Fig 8.** Maximum Safe Operating Area



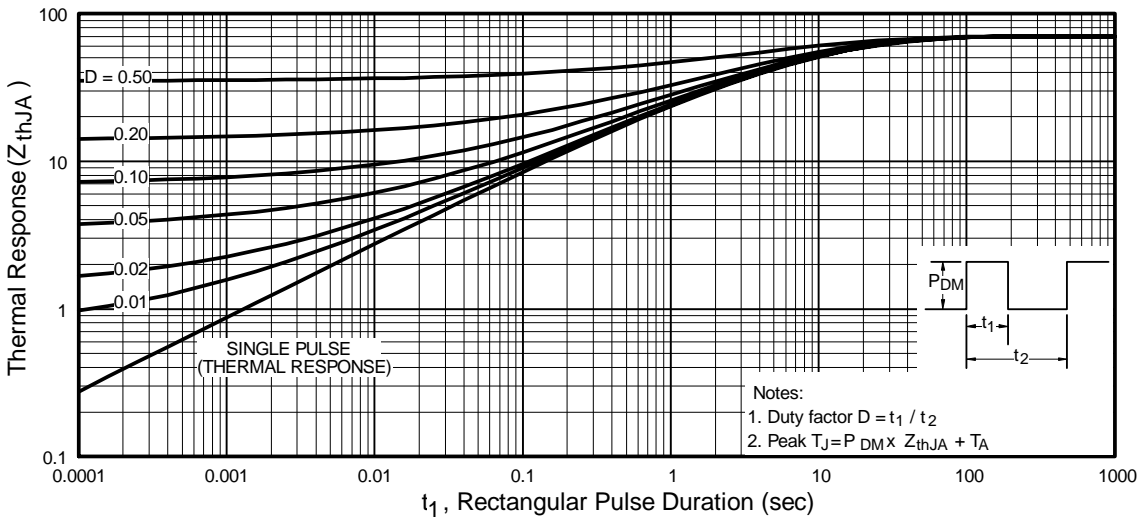
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit

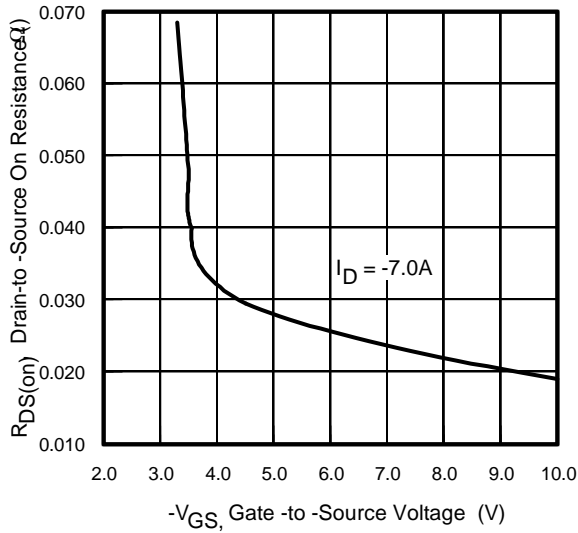


**Fig 10b.** Switching Time Waveforms

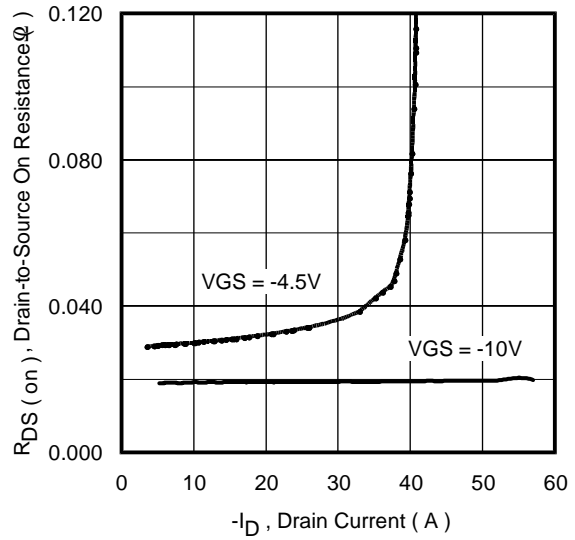


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

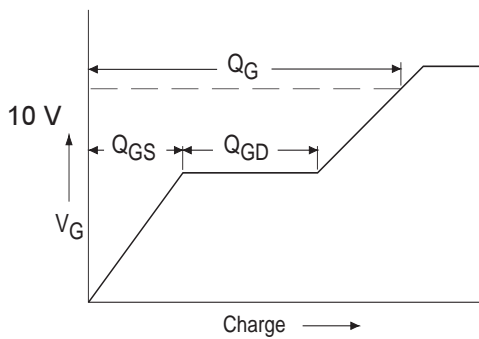
# IRF7726PbF



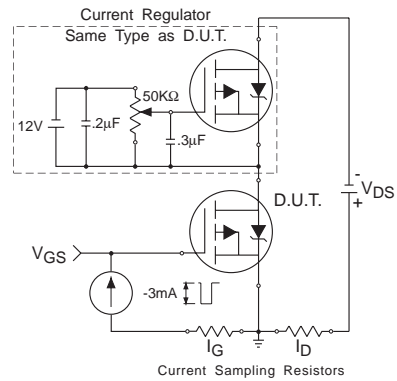
**Fig 12.** Typical On-Resistance Vs. Gate Voltage



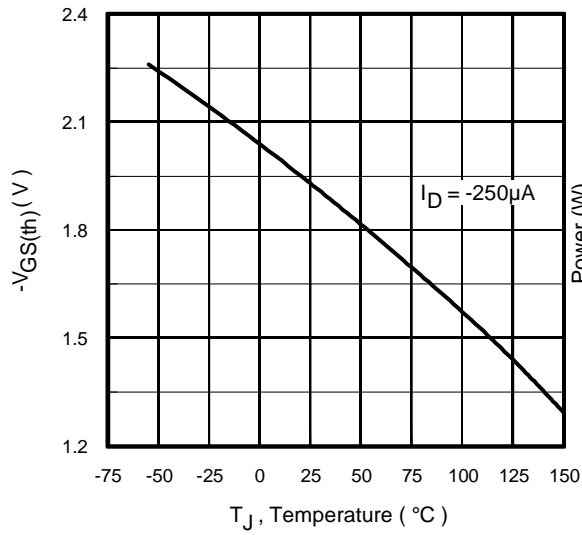
**Fig 13.** Typical On-Resistance Vs. Drain Current



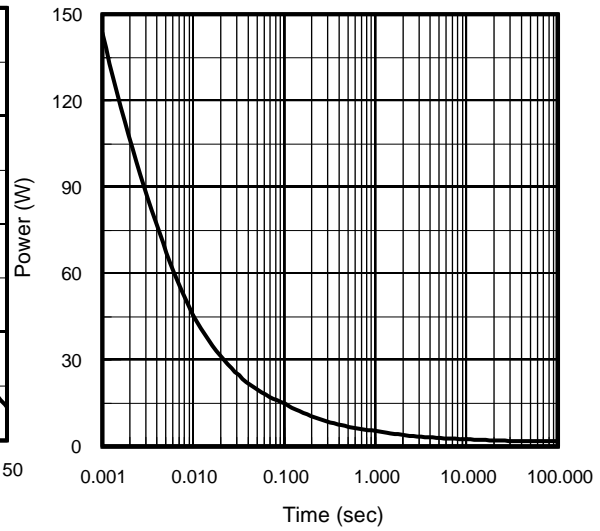
**Fig 14a.** Basic Gate Charge Waveform



**Fig 14b.** Gate Charge Test Circuit

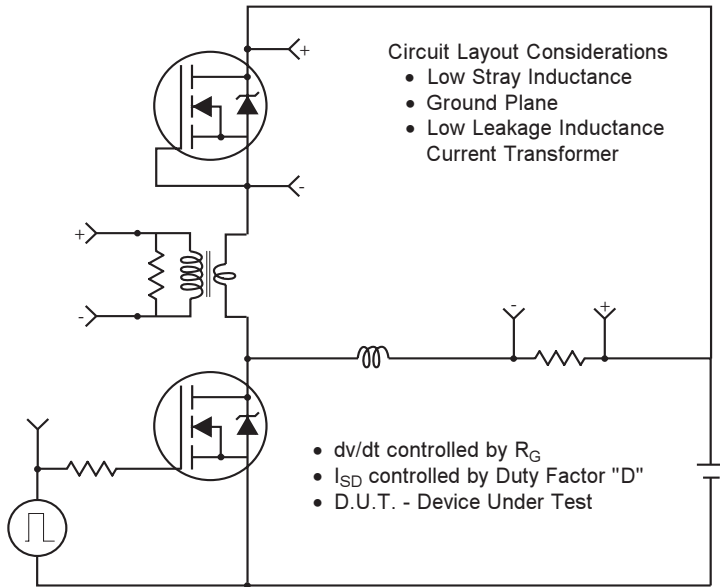


**Fig 15.** Typical V<sub>GS(th)</sub> Vs. Junction Temperature



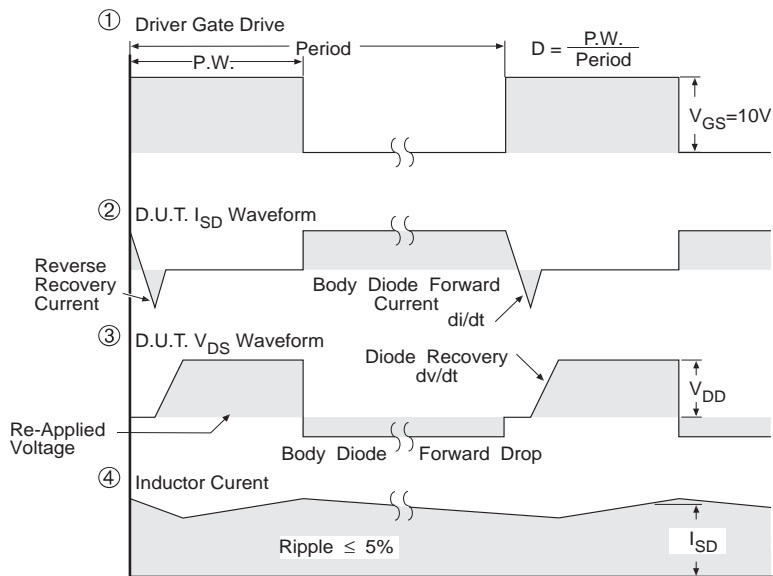
**Fig 16.** Typical Power Vs. Time

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity for P-Channel

\*\* Use P-Channel Driver for P-Channel Measurements



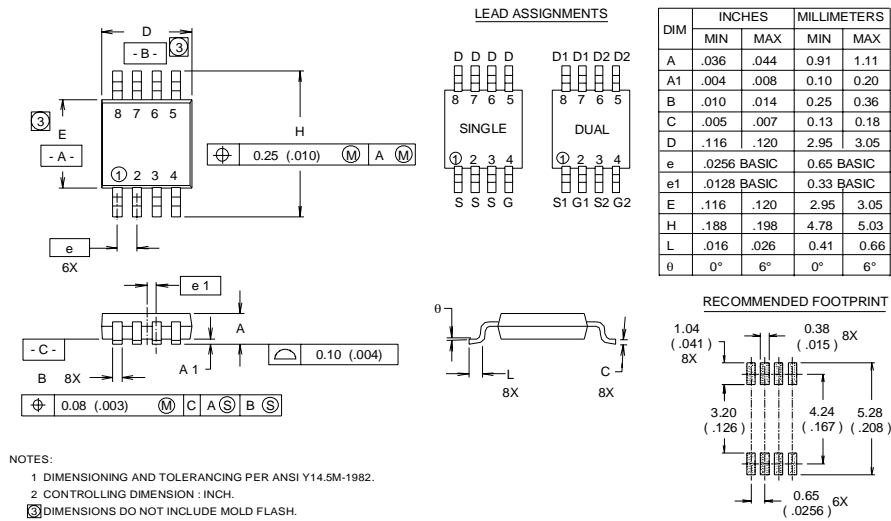
\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig 17 For P Channel HEXFETS**



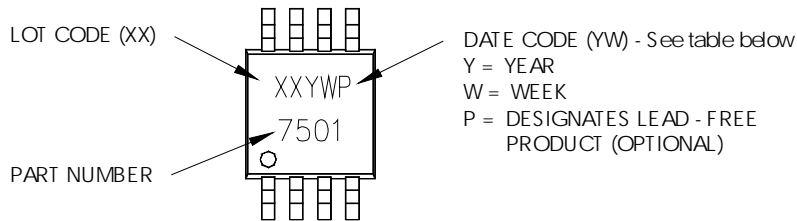
## Micro8 Package Outline

Dimensions are shown in millimeters (inches)



## Micro8 Part Marking Information

EXAMPLE: THIS IS AN IRF 7501



WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
2006	6		
2007	7		
2008	8		
2009	9		
2010	0	24	X
		25	Y
		26	Z

WW = (27-52) IF PRECEDED BY A LETTER

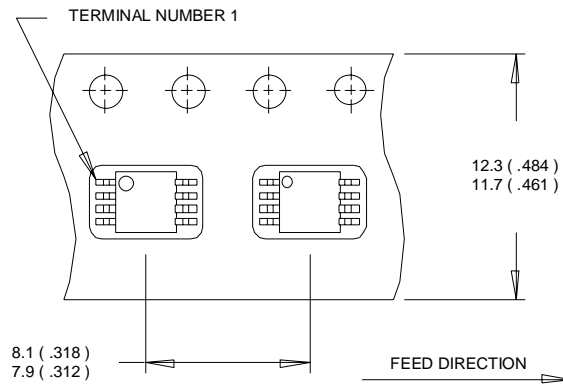
YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
2006	F		
2007	G		
2008	H		
2009	J		
2010	K	50	X
		51	Y
		52	Z

# IRF7726PbF

International  
**IR** Rectifier

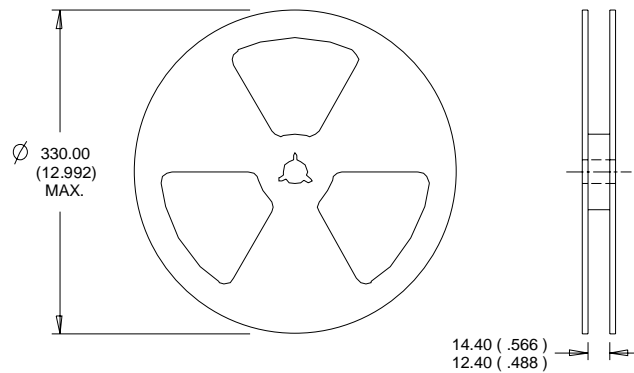
## Micro8 Tape & Reel Information

Dimensions are shown in millimeters (inches)



**NOTES:**

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.
2. CONTROLLING DIMENSION : MILLIMETER.



**NOTES:**

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualifications Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.02/05

[www.irf.com](http://www.irf.com)